

Silicon TVS Diode

Features

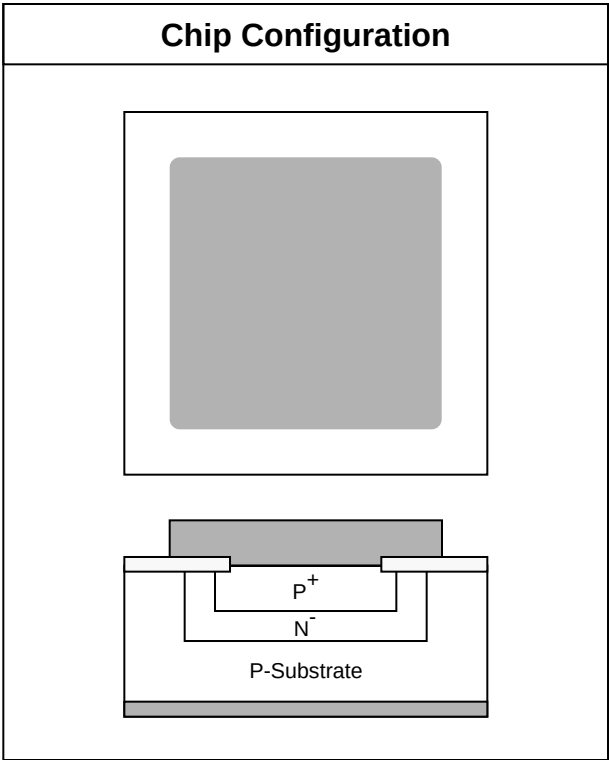
- ESD Protection
 - IEC61000-4-2 : $\pm 10\text{kV}$ (Contact Discharge)
- Low leakage current

Structure

- Bidirectional Vertical Structure
- Top electrode : Gold
- Bottom electrode : Gold

Size

- Chip size : $150(\pm 15)\mu\text{m} \times 150(\pm 15)\mu\text{m}$
- Thickness : $100(\pm 15)\mu\text{m}$
- Pad size : $100(\pm 5)\mu\text{m} \times 100(\pm 5)\mu\text{m}$



Electrical Characteristics (Ta = 25℃)

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 5\text{ mA}$	6.0	6.6	7.5	V
Forward Leakage Current	I_F	$V_F = 4\text{ V}$	-	-	100	nA
Reverse Voltage	V_Z	$I_Z = 5\text{ mA}$	6.0	6.6	7.5	V
Reverse Leakage Current	I_R	$V_R = 4\text{ V}$	-	-	100	nA

Absolute Maximum Rating (Ta = 25℃)

Parameter	Symbol	Maximum Rating	Unit
Power dissipation	P_d	30	mW
Junction Temperature	I_J	150	℃

Equivalent Circuit

